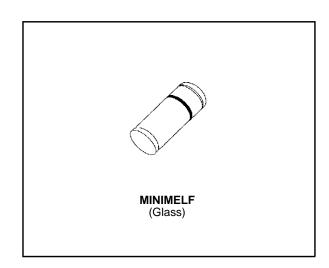


TMMBAT 45

SMALL SIGNAL SCHOTTKY DIODE



DESCRIPTION

Metal to silicon junction diode primarly intended for UHF mixers and ultrafast switching applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	15	V
lF	Forward Continuous Current	30	mA
I _{FSM}	Surge non Repetitive Forward Current	60	mA
T _{stg} T _j	Storage and Junction Temperature Range	- 65 to +150 - 65 to +125	ο̈ο̈
T∟	Maximum Temperature for Soldering during 1	260	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
R _{th(j-l)}	Junction-leads	400	°C/W

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ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions			Тур.	Max.	Unit
V_{BR}	$T_{amb} = 25^{\circ}C$	$I_R = 10\mu A$	15			V
V _F (1)	T _{amb} = 25°C	$I_F = 1mA$			0.38	V
	T _{amb} = 25°C	I _F = 10mA			0.5	
	T _{amb} = 25°C	I _F = 30mA			1	
I _R (1)	Tamb = 25°C	V _R = 6V			0.1	μΑ

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Тур.	Max.	Unit
С	T _{amb} = 25°C	$V_R = 1V$	f = 1MHz			1.1	pF
τ	T _{amb} = 25°C	$I_F = 20mA$	Krakauer Method			100	ps
F (2)	T _{amb} = 25°C	f = 1GHz			6	7	dB

- intermediate frequency amplifier, tuned on 30MHz, has a noise figure 1.5dB

Matched batches available on request. Test conditions (forward voltage and/or capacitance) according to customer specification.

 ⁽¹⁾ Pulse test: t_p≤ 300μs δ< 2%.
 (2) Noise figure test:

 diode is inserted in a tuned stripline circuit

local oscillator frequency 1GHz
 local oscillator power 1mW

Figure 1. Forward current versus forward voltage (typical values).

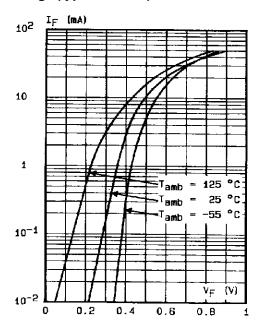


Figure 2. Capacitance C versus reverse applied voltage $V_{\mbox{\scriptsize R}}$ (typical values).

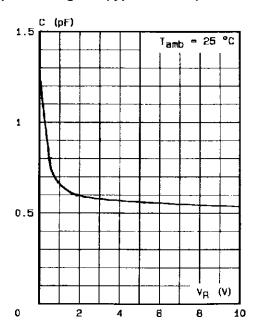


Figure 3. Reverse current versus ambient temperature.

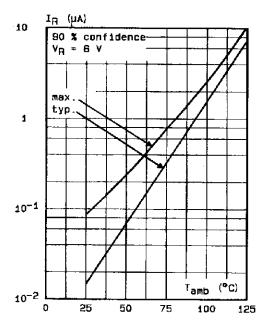
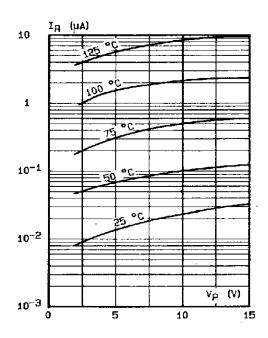


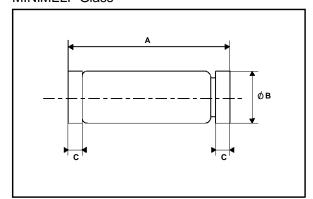
Figure 4. Reverse current versus continuous reverse voltage (typical values).

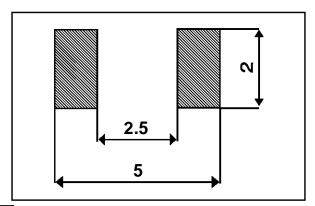


PACKAGE MECHANICAL DATA

FOOT PRINT DIMENSIONS (Millimeter)

MINIMELF Glass





	DIMENSIONS				
REF.	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
Α	3.3	3.6	0.130	0.142	
В	1.59	1.62	0.063	0.064	
С	0.4	0.5	0.016	0.020	

Marking: ring at cathode end. Weight: 0.05g

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